

Abstract of the Disclosure:

A test structure allows determining a short circuit between trench capacitors in a memory cell array in which the trench capacitors are arranged in matrix form. The test structure  
5 has, in two rows of trench capacitors, a connection of the trench capacitors of each row by tunnel structures and/or bridge structures. A contact area for contact connection is provided at each end section of a trench capacitor row.

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